

# SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

# 2SC3332 — NPN Epitaxial Planar Silicon Transistor

# **High-Voltage Switching Applications**

#### **Features**

- · Hgih breakdown voltage
- · Excellent hFE linearity
- · Wide ASO and highly resistant to breakdown
- · Adoption of MBIT process

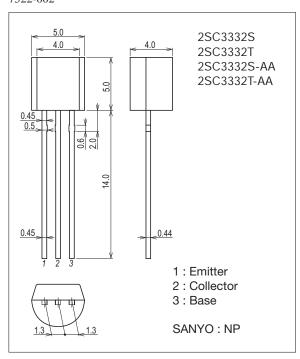
## **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		180	V
Collector-to-Emitter Voltage	VCEO		160	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	IC		0.7	Α
Collector Current (Pulse)	ICP		1.5	Α
Collector Dissipation	PC		700	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### **Package Dimensions**

unit : mm (typ) 7522-002



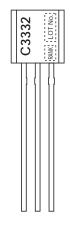
#### **Product & Package Information**

• Package : NP

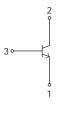
• JEITA, JEDEC : SC-34A, TO-92, TO-226AA, SOT-54

• Minimum Packing Quantity : 1,500 pcs./box, 500pcs./bag

## Marking



# **Electrical Connection**



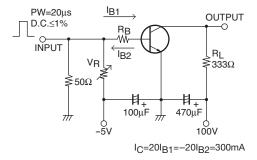
#### Electrical Characteristics at Ta=25°C

Parameter	Cumbal	Conditions			Unit	
Parameter	Parameter Symbol Conditions		min	typ	max	UIIII
Collector Cutoff Current	ICBO	V <sub>CB</sub> =120V, I <sub>E</sub> =0A			0.1	μΑ
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =4V, I <sub>C</sub> =0A			0.1	μΑ
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =5V, I <sub>C</sub> =100mA	100*		400*	
DC Current Gain	h <sub>FE</sub> 2	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	80			
Gain-Bandwidth Product	fŢ	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA		120		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V		8		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =250mA, I <sub>B</sub> =25mA		0.12	0.4	V
Base-to-Emitter Saturation Voltage	V <sub>BE</sub> (sat)	I <sub>C</sub> =250mA, I <sub>B</sub> =25mA		0.85	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0A	180			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	160			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =10μA, I <sub>C</sub> =0A	6			V
Turn-ON Time	ton			50		ns
Storage Time	tstg	See specified Test Circuit.		1000		ns
Fall Time	tf			60		ns

#### \*: The 2SC3332 is classified by 100mA hFE as follows:

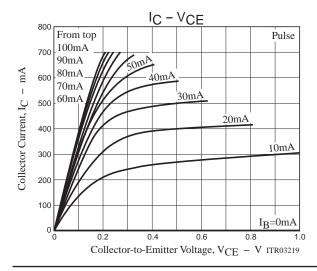
Rank	R	S	T
hFE	100 to 200	140 to 280	200 to 400

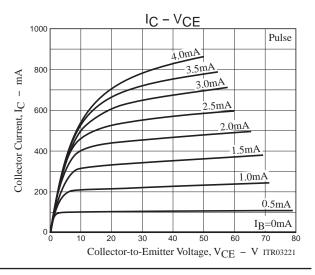
## **Switching Time Test Circuit**

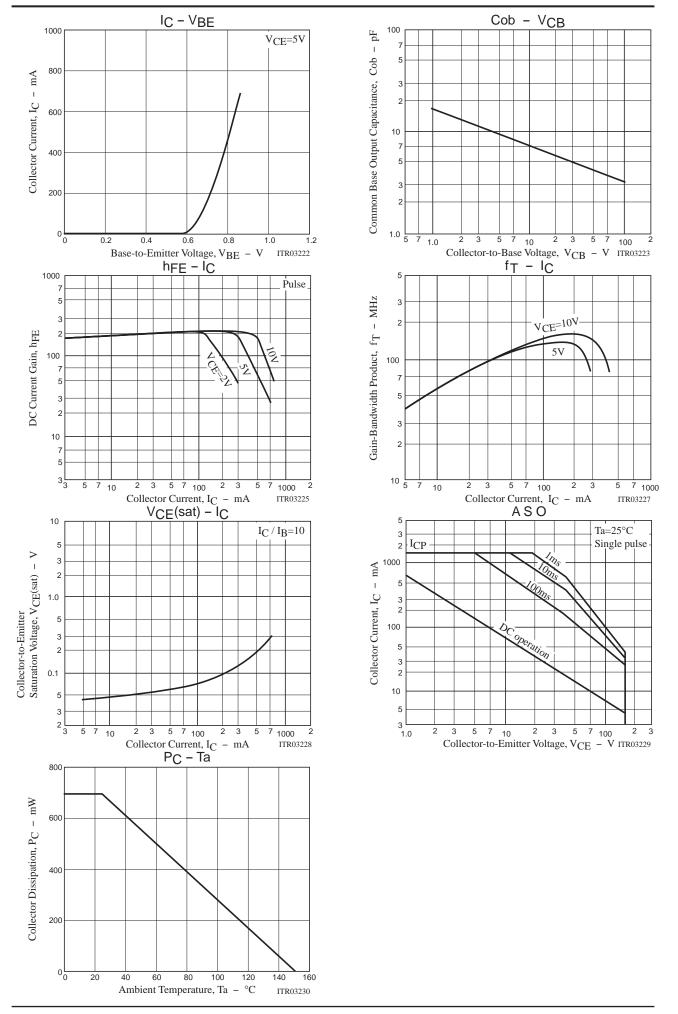


## **Ordering Information**

Device	Package	Shipping	memo
2SC3332S	NP	500pcs./bag	
2SC3332T	NP	500pcs./bag	Pb Free
2SC3332S-AA	NP	1,500pcs./box	Pb Flee
2SC3332T-AA	NP	1,500pcs./box	





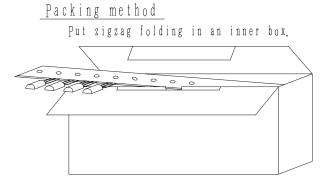


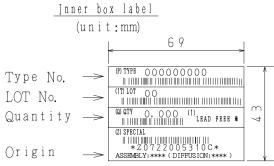
#### **Taping Specification**

#### 2SC3332S-AA, 2SC3332T-AA

# 1. Packing Format

Package Name	Packing Type	Maximum Number of devices contained (pcs	s)	Packing format
		Inner BOX (C-2) number	er of ained	Outer BOX $(C-6)$
N P	A A	Dimensions:mm (external) 1, 5		16 inner boxes contained (24, 000pcs) Dimensions:mm (external) 585 × 345 × 200



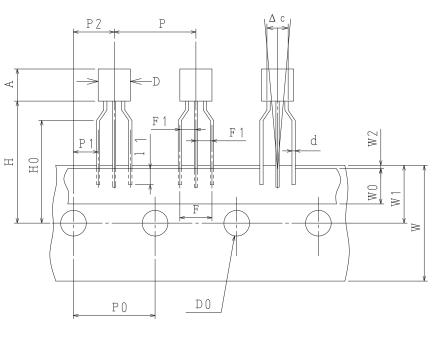


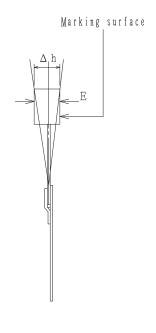
NOTE (1)

The LEAD FREE \* description shows that the surface treatment of the terminal is lead free.

Label			JEITA Phase
LEAD	FREE	3	JEITA Phase 3A
LEAD	FREE	4	JEITA Phase 3

# 2. Taping specifications2-1. Carrier tape size







# 2-2. Taping size standard

11	n	1	+	٠	mm
u	II	1	l	٠	111111

I t em	Symbol	Standard	Tolerance	
Wark niggs autoide diemeter	D	5.0	±0.2	
Work piece outside diameter	E	4.0	±0.2	
Work piece height	А	5.0	±0.2	
Lead wire diameter	d	0. 45×0. 44t	±0.1	
Bonded lead wire	1 1	2. OMIN		
Pitch between products	Р	12. 7	±0.5	
Pitch between perforations	P 0	12. 7	±0.2	
Distance between lead wire	F	5.0	+0.8 -0.2	
Lead wire pitch distance	F 1	2.5	+0.2 -0.1	
Product inclination	∆h	0	±2.0	
Displacement of perforation	P 1	3, 85	±0.3	N t
Displacement of perforations	P 2	6 35	±0.3	

Displacement of tape

W 2 0.5MAX

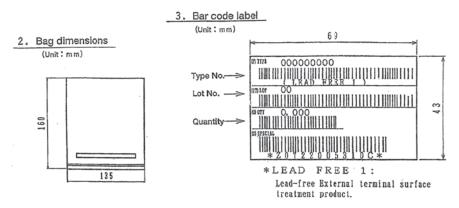
[tem	Symbol	Standard	Tolerance
Tape width	W	18 0	+ 1. 0 - 0. 5
Adhesive tape	WO	6.0	±1.5
Displacement of perforations	W 1	9. 0	±0.5
Work piece bottom surface position	Н	19. 0	± 1. 0
Insert stopper position	Н0	16 0	±0.5
Work piece upper limit position	H 1	24 5	±1.5
Perforations diameter	DO	φ4. ()	±0.2
Tape thickness	t	0.6	±0.2
Product inclination	Δc	0	± 1. 0

#### **Bag Packing Specification**

2SC3332S, 2SC3332T

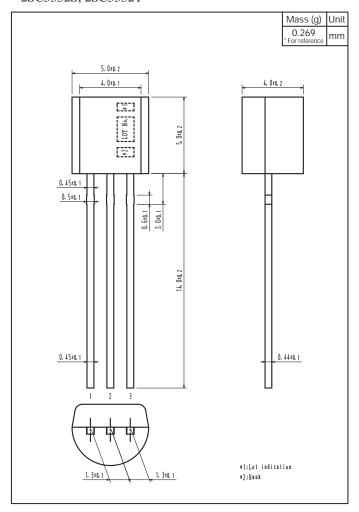
# 1 . Packing condition

Storange package		Maximum number of devices contained (ocs.)		Packing condition		
outline name	Bags	Inner box	Davices contained	Outer box ( A-1 )	outer box ( A-2 )	
NP	500	B-1 Inner box dimensions : mm (external) 4 4 5 × 2 2 5 × 5 5		5 inner boxes contained i50, 000 3 Outer box dimensions : mm (external) Ot 470 × 250 × 300 47	inner boxes contained 30, 000 uter box dimensions : mm (external) 70 × 250 × 190	



## **Outline Drawing**

2SC3332S, 2SC3332T



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